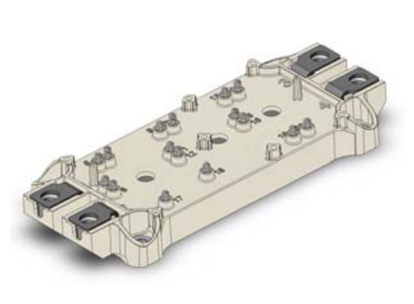
SEMiX603GAR066HDs



SEMiX® 3s

Trench IGBT Modules

SEMiX603GAR066HDs

Features

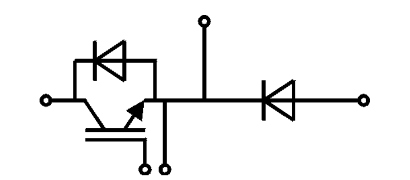
- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- UL recognised file no. E63532

Typical Applications*

- Matrix Converter
- Resonant Inverter
- Current Source Inverter

Remarks

- Case temperature limited to T_C=125°C max.
- Product reliability results are valid for T_j=150°C
- For short circuit: Soft R_{Goff} recommended
- Take care of over-voltage caused by stray inductance



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Absolute Maximum Ratings

Symbol	Conditions		Values	Unit
IGBT				
V_{CES}			600	V
I_C	T_j = 175 °C	T_c = 25 °C	720	A
		T_c = 80 °C	541	A
I_{Cnom}			600	A
I_{CRM}	I_{CRM} = 2xI_{Cnom}		1200	A
V_{GES}			-20 ... 20	V
t_{psc}	V_{CC} = 360 V V_{GE} ≤ 15 V V_{CES} ≤ 600 V	T_j = 150 °C	6	µs
T_j			-40 ... 175	°C
Inverse diode				
I_F	T_j = 175 °C	T_c = 25 °C	771	A
		T_c = 80 °C	562	A
I_{Fnom}			600	A
I_{FRM}	I_{FRM} = 2xI_{Fnom}		1200	A
I_{FSM}	t_p = 10 ms, sin 180°, T_j = 25 °C		1800	A
T_j			-40 ... 175	°C
Freewheeling diode				
I_F	T_j = 175 °C	T_c = 25 °C	771	A
		T_c = 80 °C	562	A
I_{Fnom}			600	A
I_{FRM}	I_{FRM} = 2xI_{Fnom}		1200	A
I_{FSM}	t_p = 10 ms, sin 180°, T_j = 25 °C		1800	A
T_j			-40 ... 175	°C
Module				
$I_{t(RMS)}$			600	A
T_{stg}			-40 ... 125	°C
V_{isol}	AC sinus 50Hz, t = 1 min		4000	V

Characteristics

Symbol	Conditions		min.	typ.	max.	Unit
IGBT						
$V_{CE(sat)}$	I_C = 600 A V_{GE} = 15 V chiplevel	T_j = 25 °C		1.45	1.85	V
		T_j = 150 °C		1.7	2.1	V
V_{CE0}		T_j = 25 °C		0.9	1	V
		T_j = 150 °C		0.85	0.9	V
r_{CE}	V_{GE} = 15 V	T_j = 25 °C		0.9	1.4	mΩ
		T_j = 150 °C		1.4	2.0	mΩ
$V_{GE(th)}$	V_{GE}=V_{CE}, I_C = 9.6 mA		5	5.8	6.5	V
I_{CES}	V_{GE} = 0 V V_{CE} = 600 V	T_j = 25 °C		0.15	0.45	mA
		T_j = 150 °C				mA
C_{ies}	V_{CE} = 25 V V_{GE} = 0 V	f = 1 MHz		37.0		nF
C_{oes}		f = 1 MHz		2.31		nF
C_{res}		f = 1 MHz		1.10		nF
Q_G	V_{GE} = - 8 V...+ 15 V			4800		nC
R_{Gint}	T_j = 25 °C			0.67		Ω

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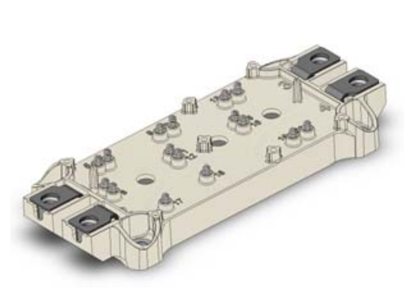

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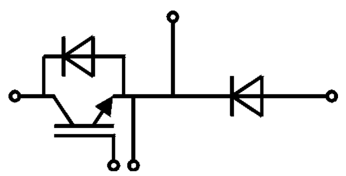

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Characteristics						
Symbol	**Conditions**		**min.**	**typ.**	**max.**	**Unit**
$t_{d(on)}$	V_{CC} = 300 V	T_j = 150 °C		150		ns
t_r	I_C = 600 A	T_j = 150 °C		145		ns
E_{on}	$R_{G\ on}$ = 3 Ω	T_j = 150 °C		12		mJ
$t_{d(off)}$	$R_{G\ off}$ = 3 Ω	T_j = 150 °C		1050		ns
t_f		T_j = 150 °C		105		ns
E_{off}		T_j = 150 °C		43		mJ
$R_{th(j-c)}$	per IGBT				0.087	K/W
Inverse diode						
$V_F = V_{EC}$	I_F = 600 A	T_j = 25 °C		1.4	1.60	V
	V_{GE} = 0 V chip	T_j = 150 °C		1.4	1.6	V
V_{F0}		T_j = 25 °C	0.9	1	1.1	V
		T_j = 150 °C	0.75	0.85	0.95	V
r_F		T_j = 25 °C	0.5	0.7	0.8	mΩ
		T_j = 150 °C	0.8	0.9	1.1	mΩ
I_{RRM}	I_F = 600 A	T_j = 150 °C		350		A
Q_{rr}	di/dt_{off} = 3800 A/µs	T_j = 150 °C		63		µC
E_{rr}	V_{GE} = -8 V V_{CC} = 300 V	T_j = 150 °C		13		mJ
$R_{th(j-c)}$	per diode				0.11	K/W
Freewheeling diode						
$V_F = V_{EC}$	I_F = 600 A	T_j = 25 °C		1.4	1.6	V
	V_{GE} = 0 V chip	T_j = 150 °C		1.4	1.6	V
V_{F0}		T_j = 25 °C	0.9	1	1.1	V
		T_j = 150 °C	0.75	0.85	0.95	V
r_F		T_j = 25 °C	0.5	0.7	0.8	mΩ
		T_j = 150 °C	0.8	0.9	1.1	mΩ
I_{RRM}	I_F = 600 A	T_j = 150 °C		350		A
Q_{rr}	di/dt_{off} = 3800 A/µs	T_j = 150 °C		63		µC
E_{rr}	V_{GE} = -8 V V_{CC} = 300 V	T_j = 150 °C		13		mJ
$R_{th(j-c)}$	per diode				0.11	K/W
Module						
L_{CE}				20		nH
$R_{CC'+EE'}$	res., terminal-chip	T_C = 25 °C		0.7		mΩ
		T_C = 125 °C		1		mΩ
$R_{th(c-s)}$	per module			0.04		K/W
M_s	to heat sink (M5)		3		5	Nm
M_t		to terminals (M6)	2.5		5	Nm
						Nm
w					300	g
Temperatur Sensor						
R_{100}	T_c=100°C (R_{25}=5 kΩ)			493 ± 5%		Ω
$B_{100/125}$	$R_{(T)}=R_{100}exp[B_{100/125}(1/T-1/T_{100})]$; T[K];			3550 ±2%		K

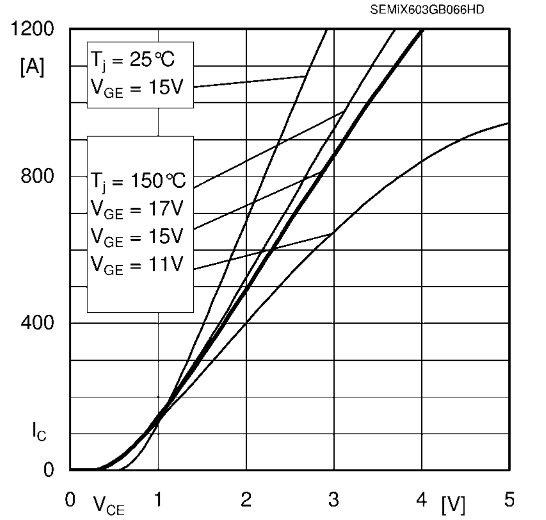

Fig. 1: Typ. output characteristic, inclusive $R_{CC'+ EE'}$

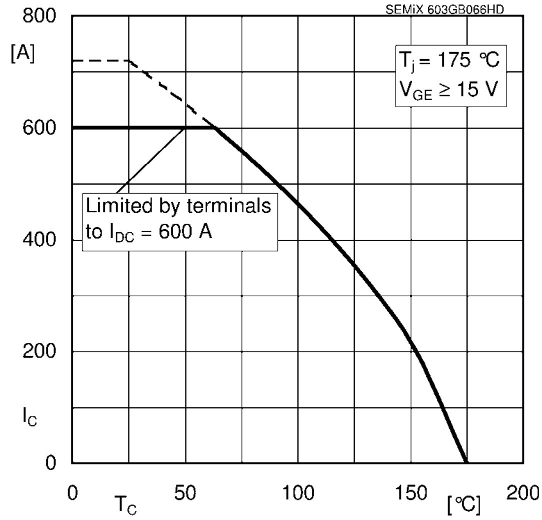

Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

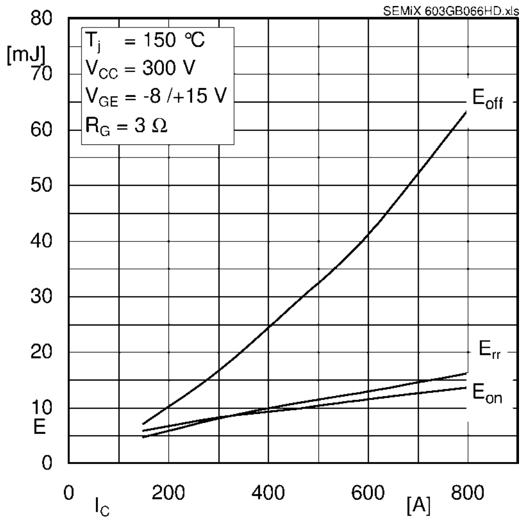

Fig. 3: Typ. turn-on /-off energy = f (I_C)

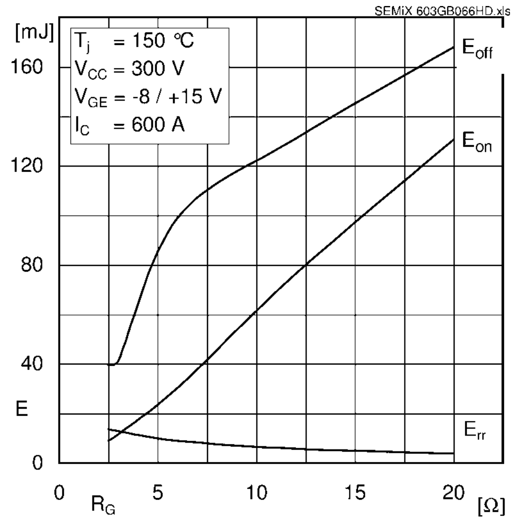

Fig. 4: Typ. turn-on /-off energy = f (R_G)

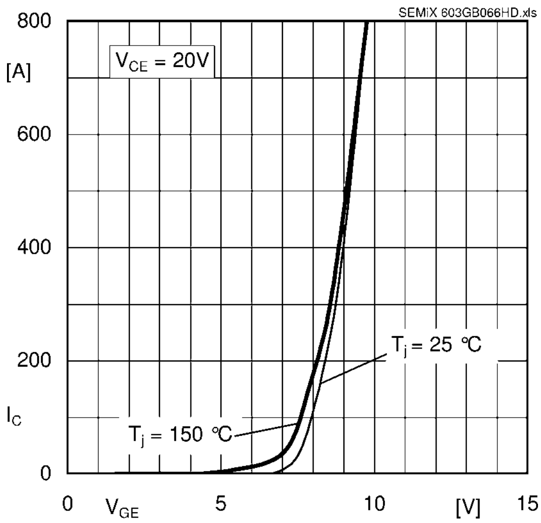

Fig. 5: Typ. transfer characteristic

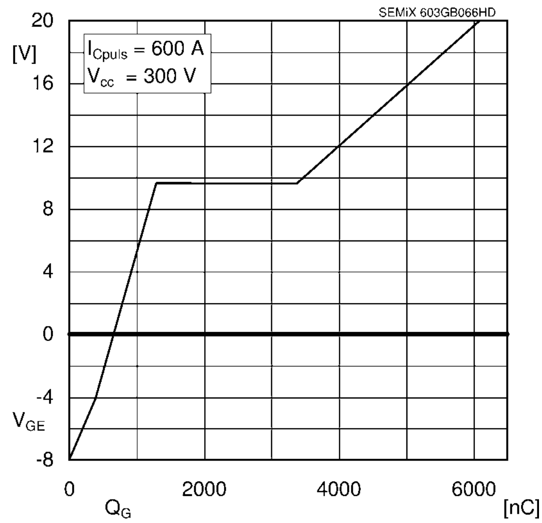

Fig. 6: Typ. gate charge characteristic

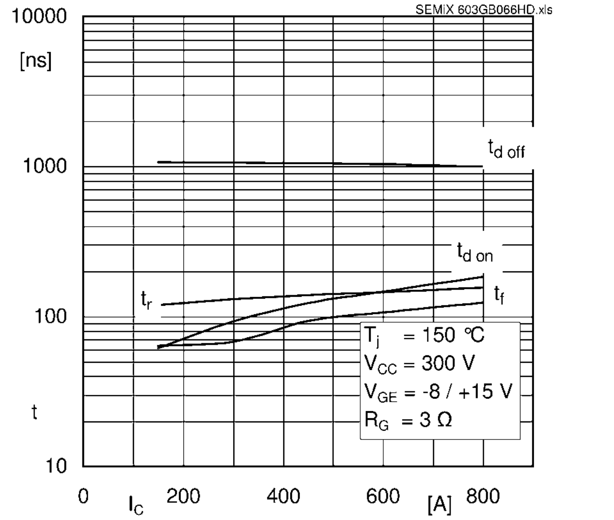

Fig. 7: Typ. switching times vs. I_C

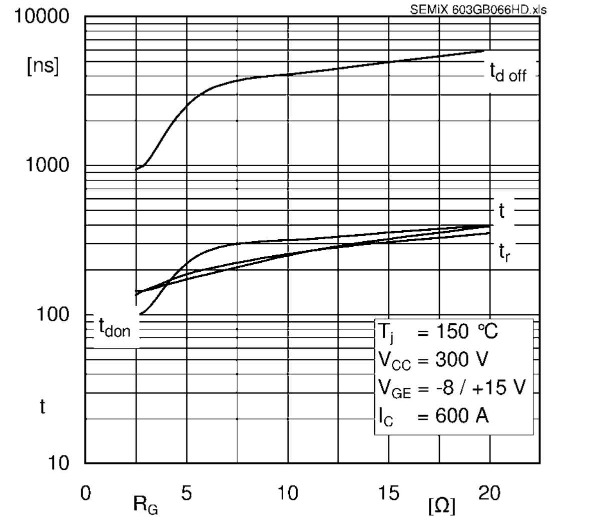

Fig. 8: Typ. switching times vs. gate resistor R_G

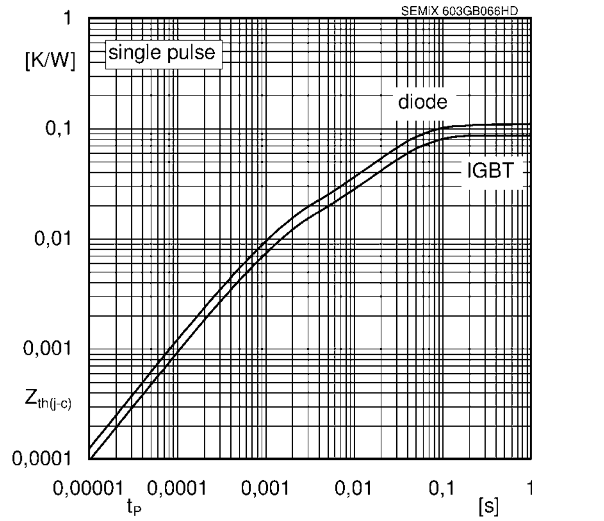

Fig. 9: Typ. transient thermal impedance

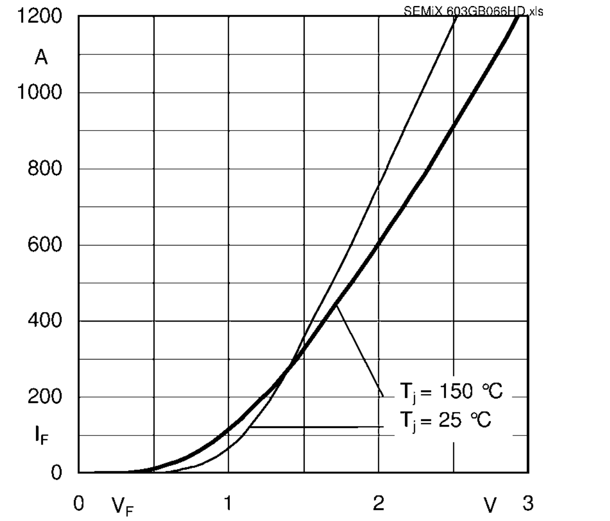

Fig. 10: Typ. CAL diode forward charact., incl. $R_{CC'+EE'}$

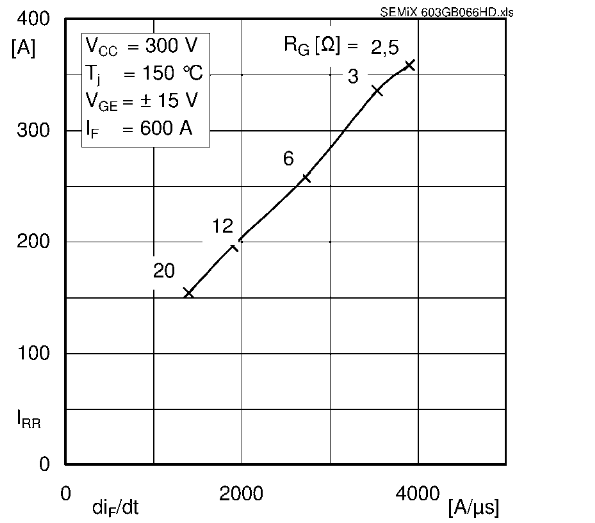

Fig. 11: Typ. CAL diode peak reverse recovery current

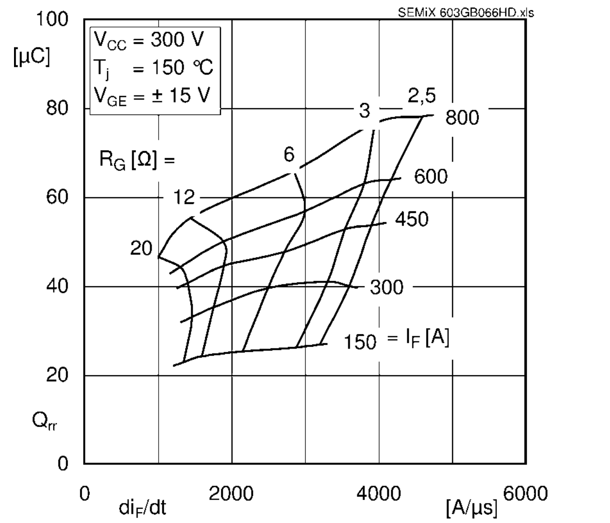

Fig. 12: Typ. CAL diode recovery charge

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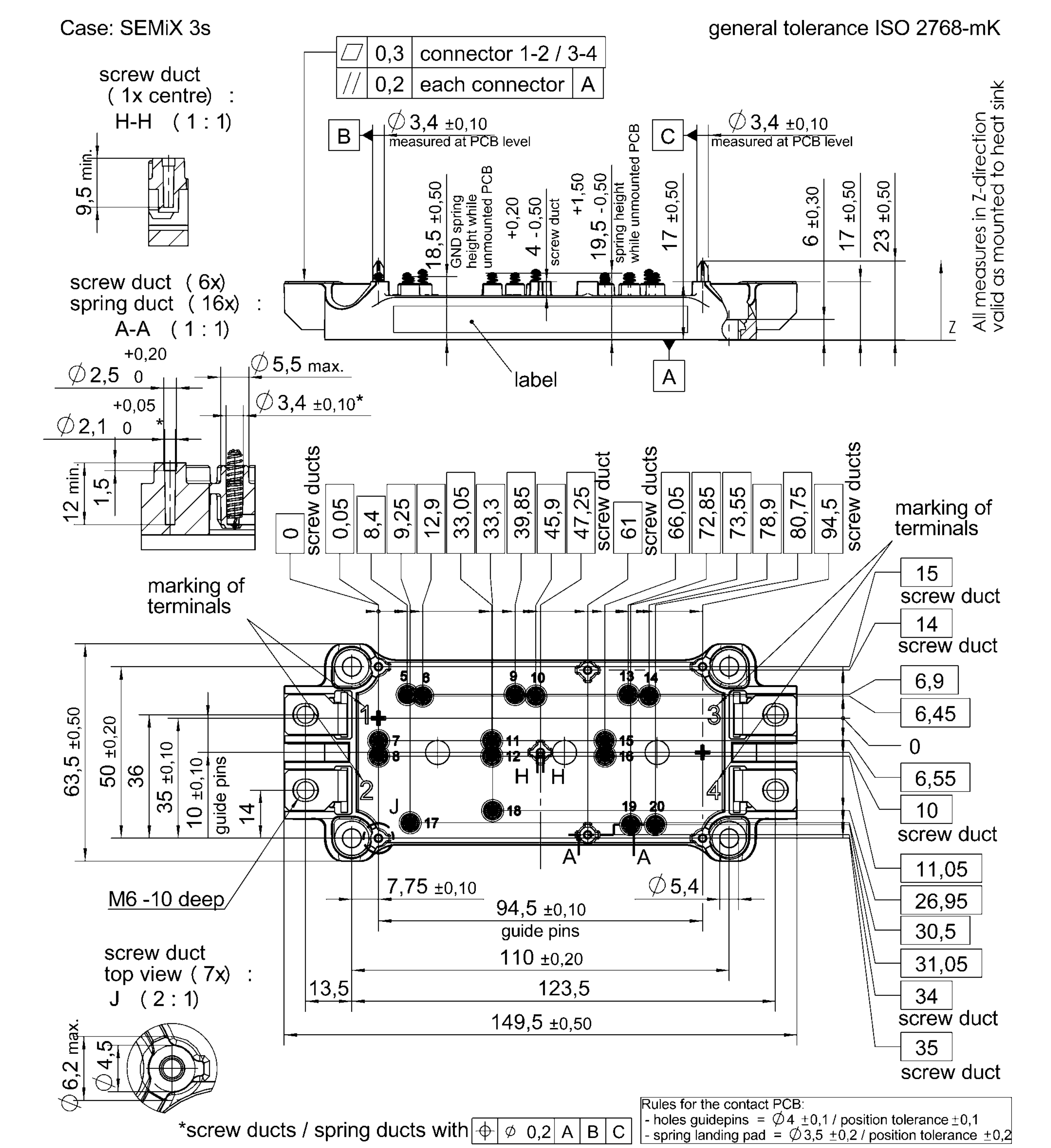

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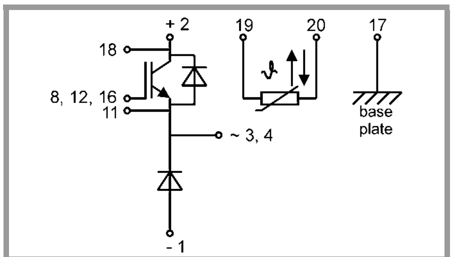

spring configuration

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